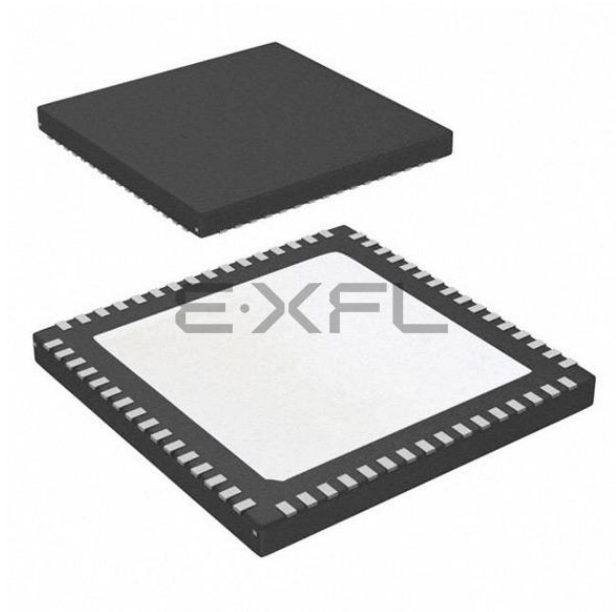
Renesas Electronics America Inc - R7FS124763A01CNB#AC0 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	CANbus, I²C, SCI, SPI, UART/USART, USB
Peripherals	LVD, POR, PWM, WDT
Number of I/O	51
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 18x14b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-WFQFN Exposed Pad
Supplier Device Package	64-HWQFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r7fs124763a01cnb-ac0

Ultra-low power 32-MHz Arm® Cortex®-M0+ microcontroller, 128-KB code flash memory, 16-KB SRAM, Capacitive Touch Sensing Unit, 14-bit A/D Converter, 12-bit D/A Converter, security and safety features.

Features

■ Arm Cortex-M0+ Core
- Armv6-M architecture
- Maximum operating frequency: 32 MHz
- Debug and Trace: DWT, BPU, CoreSight™ MTB-M0+
- CoreSight Debug Port: SW-DP

■ Memory
- 128-KB code flash memory
- 4-KB data flash memory (100,000 erase/write cycles)
- Up to 16-KB SRAM
- 128-bit unique ID

■ Connectivity
- USB 2.0 Full-Speed Module (USBFS)
  - On-chip transceiver with voltage regulator
  - Compliant with USB Battery Charging Specification 1.2
- Serial Communications Interface (SCI) × 3
  - UART
  - Simple IIC
  - Simple SPI
- Serial Peripheral Interface (SPI) × 2
- I^2C bus interface (IIC) × 2
- CAN module (CAN)

■ Analog
- 14-Bit A/D Converter (ADC14)
- 12-Bit D/A Converter (DAC12)
- Low-Power Analog Comparator (ACMPLP) × 2
- Temperature Sensor (TSN)

■ Timers
- General PWM Timer 32-Bit (GPT32)
- General PWM Timer 16-Bit (GPT16) × 6
- Asynchronous General-Purpose Timer (AGT) × 2
- Watchdog Timer (WDT)

■ Safety
- SRAM Parity Error Check
- Flash Area Protection
- ADC self-diagnosis function
- Clock Frequency Accuracy Measurement Circuit (CAC)
- Cyclic Redundancy Check (CRC) Calculator
- Data Operation Circuit (DOC)
- Port Output Enable for GPT (POEG)
- Independent Watchdog Timer (IWDT)
- GPIO Readback Level Detection
- Register Write Protection
- Main Oscillator Stop Detection

■ System and Power Management
- Low-power modes
- Realtime Clock (RTC)
- Event Link Controller (ELC)
- Data Transfer Controller (DTC)
- Key Interrupt Function (KINT)
- Power-on reset
- Low Voltage Detection with voltage settings

■ Security and Encryption
- AES128/256
- True Random Number Generator (TRNG)

■ Human Machine Interface (HMI)
- Capacitive Touch Sensing Unit (CTSU)

■ Multiple Clock Sources
- Main clock oscillator (MOSC)
  (1 to 20 MHz when VCC = 2.4 to 5.5 V)
  (1 to 8 MHz when VCC = 1.8 to 5.5 V)
  (1 to 4 MHz when VCC = 1.6 to 5.5 V)
- Sub-clock oscillator (SOSC) (32.768 kHz)
- High-speed on-chip oscillator (HOCO)
  (24, 32, 48, 64 MHz when VCC = 2.4 to 5.5 V)
  (24, 32, 48 MHz when VCC = 1.8 to 5.5 V)
  (24, 32 MHz when VCC = 1.6 to 5.5 V)
- Middle-speed on-chip oscillator (MOCO) (8 MHz)
- Low-speed on-chip oscillator (LOCO) (32.768 kHz)
- Independent watchdog timer OCO (15 kHz)
- Clock trim function for HOCO/MOCO/LOCO
- Clock out support

■ General Purpose I/O Ports
- Up to 51 input/output pins
  - Up to 3 CMOS input
  - Up to 48 CMOS input/output
    - Up to 6 input/output 5 V tolerant
    - Up to 16 pins high current (20 mA)

■ Operating Voltage
- VCC: 1.6 to 5.5 V

■ Operating Temperature and Packages
- Ta = –40°C to +85°C
  - 36-pin LGA (4 mm × 4 mm, 0.5 mm pitch)
- Ta = –40°C to +105°C
  - 64-pin LQFP (10 mm × 10 mm, 0.5 mm pitch)
  - 48-pin LQFP (7 mm × 7 mm, 0.5 mm pitch)
  - 64-pin QFN (8 mm × 8 mm, 0.4 mm pitch)
  - 48-pin QFN (7 mm × 7 mm, 0.5 mm pitch)
  - 40-pin QFN (6 mm × 6 mm, 0.5 mm pitch)

Table 1.11 Security

Feature	Functional description
AES	See section 38, AES Engine in User's Manual
True Random Number Generator (TRNG)	See section 39, True Random Number Generator (TRNG) in User's Manual

1.2 Block Diagram

Figure 1.1 shows the block diagram of the MCU superset. Individual devices within the group may have a subset of the features.

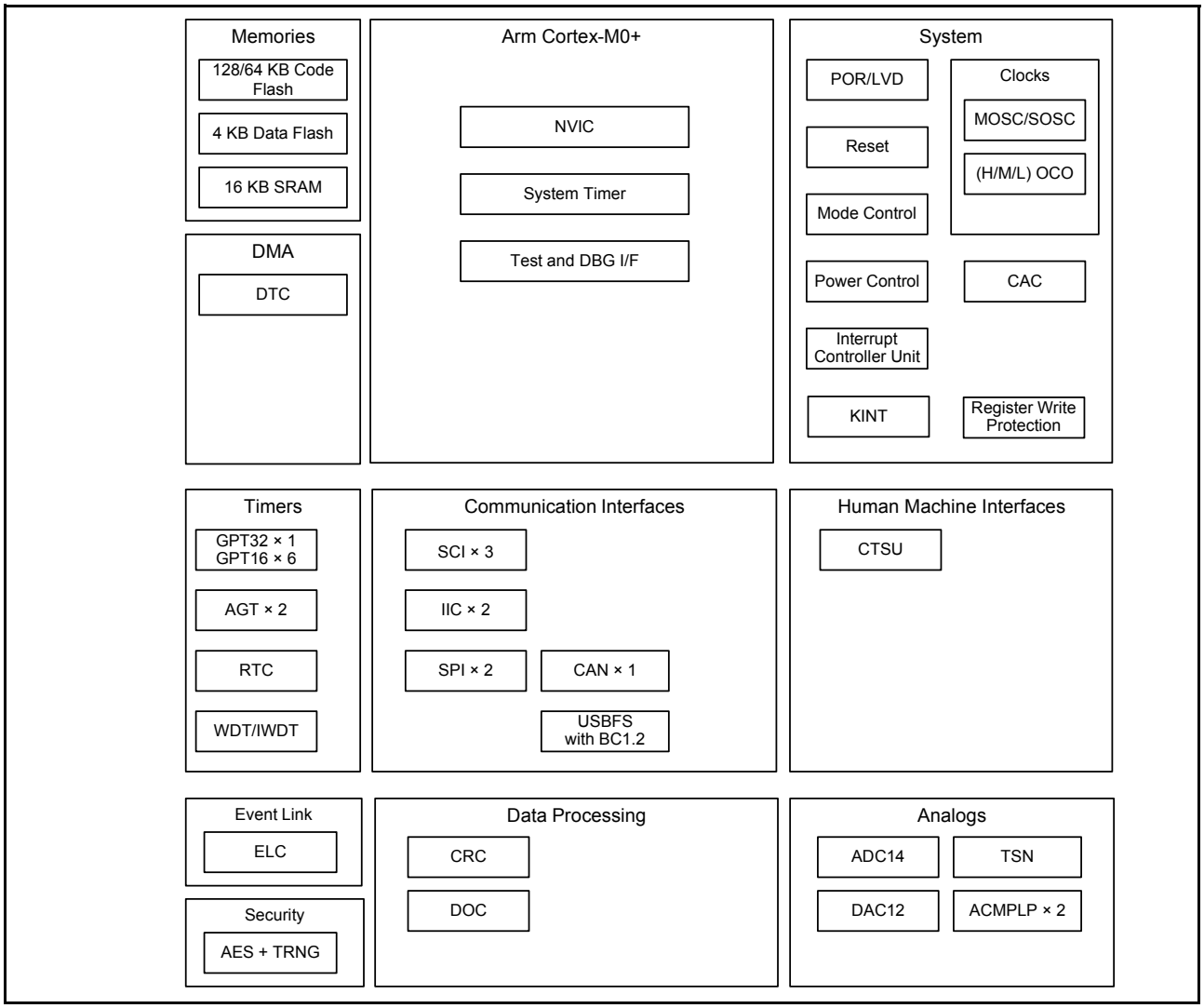

Figure 1.1 Block diagram

1.3 Part Numbering

Figure 1.2 shows how to read the product part number, memory capacity, and package types. Table 1.12 shows a list of products.

1.4 Function Comparison

Table 1.13 Function comparison

Parts number		R7FS124773A01CFM/ R7FS124763A01CFM/ R7FS124773A01CNB/	R7FS124773A01CFL/ R7FS124763A01CFL/ R7FS124773A01CNE	R7FS124773A01CNF	R7FS124772A01CLM/ R7FS124762A01CLM
Pin count		64	48	40	36
Package		LQFP/QFN	LQFP/QFN	QFN	LGA
Code flash memory		128/64 KB			
Data flash memory		4 KB			
SRAM		16 KB			
	Parity	4 KB			
System	CPU clock	32 MHz			
	ICU	Yes			
	KINT	8	5	5	4
Event link	ELC	Yes			
DMA	DTC	Yes			
Timers	GPT32	1			
	GPT16	6	6	4	4
	AGT	2	2	2	2
	RTC	Yes			
	WDT/IWDT	Yes			
Communication	SCI	3			
	IIC	2			
	SPI	2			
	CAN	Yes			
	USBFS	Yes			
Analog	ADC14	18	14	12	11
	DAC12	1			
	ACMPLP	2			
	TSN	Yes			
HMI	CTSU	31	23	17	13
	KINT	8	5	5	4
Data processing	CRC	Yes			
	DOC	Yes			
Security		AES and TRNG			

2. Electrical Characteristics

Unless otherwise specified, the electrical characteristics of the MCU are defined under the following conditions:

VCC*1 = AVCC0 = VCC_USB*2 = VCC_USB_LDO*2 = 1.6 to 5.5V, VREFH0 = 1.6 to AVCC0,

VSS = AVSS0 = VREFL0 = VSS_USB = 0 V, Ta = T_{opr}

Note 1. The typical condition is set to VCC = 3.3V.
Note 2. When USBFS is not used.

Figure 2.1 shows the timing conditions.

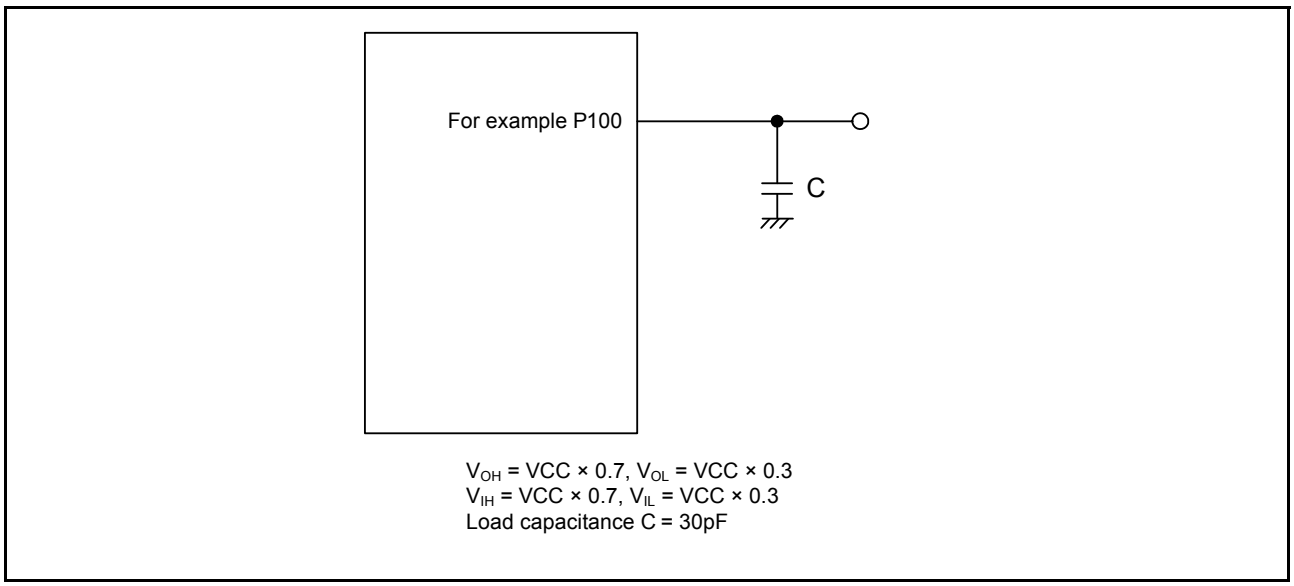

Figure 2.1 Input or output timing measurement conditions

The measurement conditions of timing specification in each peripherals are recommended for the best peripheral operation. However, make sure to adjust driving abilities of each pins to meet your conditions.

Each function pin used for the same function must select the same drive ability. If I/O drive ability of each function is mixed, the AC specification of the function is not guaranteed.

2.2.3 I/O I_{OH}, I_{OL}

Table 2.6 I/O I_{OH}, I_{OL}
Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter			Symbol	Min	Typ	Max	Unit
Permissible output current (average value per pin)	Ports P000 to P004, P010 to P015, P212, P213	-	I_{OH}	-	-	–4.0	mA
			I_{OL}	-	-	4.0	mA
	Ports P408, P409	Low drive*1	I_{OH}	-	-	–4.0	mA
			I_{OL}	-	-	4.0	mA
		Middle drive*2 VCC = 2.7 to 3.0 V	I_{OH}	-	-	–8.0	mA
			I_{OL}	-	-	8.0	mA
		Middle drive*2 VCC = 3.0 to 5.5 V	I_{OH}	-	-	–20.0	mA
			I_{OL}	-	-	20.0	mA
	Other output pins*3	Low drive*1	I_{OH}	-	-	–4.0	mA
			I_{OL}	-	-	4.0	mA
		Middle drive*2	I_{OH}	-	-	–8.0	mA
			I_{OL}	-	-	8.0	mA
Permissible output current (max value per pin)	Ports P000 to P004, P010 to P015, P212, P213	-	I_{OH}	-	-	–4.0	mA
			I_{OL}	-	-	4.0	mA
	Ports P408, P409	Low drive*1	I_{OH}	-	-	–4.0	mA
			I_{OL}	-	-	4.0	mA
		Middle drive*2 VCC = 2.7 to 3.0 V	I_{OH}	-	-	–8.0	mA
			I_{OL}	-	-	8.0	mA
		Middle drive*2 VCC = 3.0 to 5.5 V	I_{OH}	-	-	–20.0	mA
			I_{OL}	-	-	20.0	mA
	Other output pins*3	Low drive*1	I_{OH}	-	-	–4.0	mA
			I_{OL}	-	-	4.0	mA
		Middle drive*2	I_{OH}	-	-	–8.0	mA
			I_{OL}	-	-	8.0	mA
Permissible output current (max value total pins)	Total of ports P000 to P004, P010 to P015		$\Sigma I_{OH\ (max)}$	-	-	–30	mA
			$\Sigma I_{OL\ (max)}$	-	-	30	mA
	Total of all output pin		$\Sigma I_{OH\ (max)}$	-	-	–60	mA
			$\Sigma I_{OL\ (max)}$	-	-	60	mA

Caution: To protect the reliability of the MCU, the output current values should not exceed the values in this table. The average output current indicates the average value of current measured during 100 µs.

Note 1. This is the value when low driving ability is selected with the Port Drive Capability bit in the PmnPFS register.

Note 2. This is the value when middle driving ability is selected with the Port Drive Capability bit in the register.

Note 3. Except for Ports P200, P214, P215, which are input ports.

2.2.4 I/O V_{OH}, V_{OL}, and Other Characteristics

Table 2.7 I/O V_{OH}, V_{OL} (1)
Conditions: VCC = AVCC0 = 4.0 to 5.5 V

Parameter			Symbol	Min	Typ	Max	Unit	Test conditions
Output voltage	IIC*1, *2		V_{OL}	-	-	0.4	V	I_{OL} = 3.0 mA
			V_{OL}	-	-	0.6		I_{OL} = 6.0 mA
	Ports P408, P409*2, *3		V_{OH}	VCC – 1.0	-	-		I_{OH} = –20 mA
			V_{OL}	-	-	1.0		I_{OL} = 20 mA
	Ports P000 to P004 P010 to P015	Low drive	V_{OH}	AVCC0 – 0.8	-			I_{OH} = –2.0 mA
			V_{OL}	-	-	0.8		I_{OL} = 2.0 mA
		Middle drive	V_{OH}	AVCC0 – 0.8	-			I_{OH} = –4.0 mA
			V_{OL}	-	-	0.8		I_{OL} = 4.0 mA
	Other output pins*4	Low drive	V_{OH}	VCC – 0.8	-	-		I_{OH} = –2.0 mA
			V_{OL}	-	-	0.8		I_{OL} = 2.0 mA
		Middle drive*5	V_{OH}	VCC – 0.8	-	-		I_{OH} = –4.0 mA
			V_{OL}	-	-	0.8		I_{OL} = 4.0 mA

Note 1. SCL0_A, SDA0_A, SCL0_B, SDA0_B, SCL1_A, SDA1_A, SCL1_B, SDA1_B (total 8 pins).
Note 2. This is the value when middle driving ability is selected with the Port Drive Capability bit in the PmnPFS register.
Note 3. Based on characterization data, not tested in production.
Note 4. Except for Ports P200, P214, and P215, which are input ports.
Note 5. Except for P212, P213.

Table 2.8 I/O V_{OH}, V_{OL} (2)
Conditions: VCC = AVCC0 = 2.7 to 4.0 V

Parameter			Symbol	Min	Typ	Max	Unit	Test conditions
Output voltage	IIC*1, *2		V_{OL}	-	-	0.4	V	I_{OL} = 3.0 mA
			V_{OL}	-	-	0.6		I_{OL} = 6.0 mA
	Ports P408, P409*2, *3		V_{OH}	VCC – 1.0	-	-		I_{OH} = –20 mA VCC = 3.3 V
			V_{OL}	-	-	1.0		I_{OL} = 20 mA VCC = 3.3 V
	Ports P000 to P004 P010 to P015	Low drive	V_{OH}	AVCC0 – 0.5	-	-		I_{OH} = –1.0 mA
			V_{OL}	-	-	0.5		I_{OL} = 1.0 mA
		Middle drive	V_{OH}	AVCC0 – 0.5	-	-		I_{OH} = –2.0 mA
			V_{OL}	-	-	0.5		I_{OL} = 2.0 mA
	Other output pins*4	Low drive	V_{OH}	VCC – 0.5	-	-		I_{OH} = –1.0 mA
			V_{OL}	-	-	0.5		I_{OL} = 1.0 mA
		Middle drive*5	V_{OH}	VCC – 0.5	-	-		I_{OH} = –2.0 mA
			V_{OL}	-	-	0.5		I_{OL} = 2.0 mA

Note 1. SCL0_A, SDA0_A, SCL0_B, SDA0_B, SCL1_A, SDA1_A, SCL1_B, SDA1_B (total 8 pins).
Note 2. This is the value when middle driving ability is selected with the Port Drive Capability bit in the PmnPFS register.
Note 3. Based on characterization data, not tested in production.
Note 4. Except for Ports P200, P214, P215, which are input ports.
Note 5. Except for P212, P213.

Table 2.9 I/O V_{OH}, V_{OL} (3)
Conditions: VCC = AVCC0 = 1.6 to 2.7 V

Parameter			Symbol	Min	Typ	Max	Unit	Test conditions
Output voltage	Ports P000 to P004 P010 to P015	Low drive	V_{OH}	AVCC0 – 0.3	-	-		I_{OH} = –0.5 mA
			V_{OL}	-	-	0.3		I_{OL} = 0.5 mA
		Middle drive	V_{OH}	AVCC0 – 0.3	-	-		I_{OH} = –1.0 mA
			V_{OL}	-	-	0.3		I_{OL} = 1.0 mA
	Other output pins*1	Low drive	V_{OH}	VCC – 0.3	-	-	V	I_{OH} = –0.5 mA
			V_{OL}	-	-	0.3		I_{OL} = 0.5 mA
		Middle drive*2	V_{OH}	VCC – 0.3	-	-		I_{OH} = –1.0 mA
			V_{OL}	-	-	0.3		I_{OL} = 1.0 mA

Note 1. Except for Ports P200, P214, P215, which are input ports.
Note 2. Except for P212, P213.

Table 2.10 I/O other characteristics
Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
Input leakage current	RES, Ports P200, P214, P215	$\lvert I_{in} \rvert$	-	-	1.0	µA	V_{in} = 0 V V_{in} = VCC
Three-state leakage current (off state)	5V-tolerant ports	$\lvert I_{TSI} \rvert$	-	-	1.0	µA	V_{in} = 0 V V_{in} = 5.8 V
	Other ports		-	-	1.0		V_{in} = 0 V V_{in} = VCC
Input pull-up resistor	All ports (except for P200, P214, P215)	R_U	10	20	50	kΩ	V_{in} = 0 V
Input capacitance	USB_DP, USB_DM, P200	C_{in}	-	-	30	pF	V_{in} = 0 V f = 1 MHz T_a = 25°C
	Other input pins		-	-	15		

2.2.5 I/O Pin Output Characteristics of Low Drive Capacity

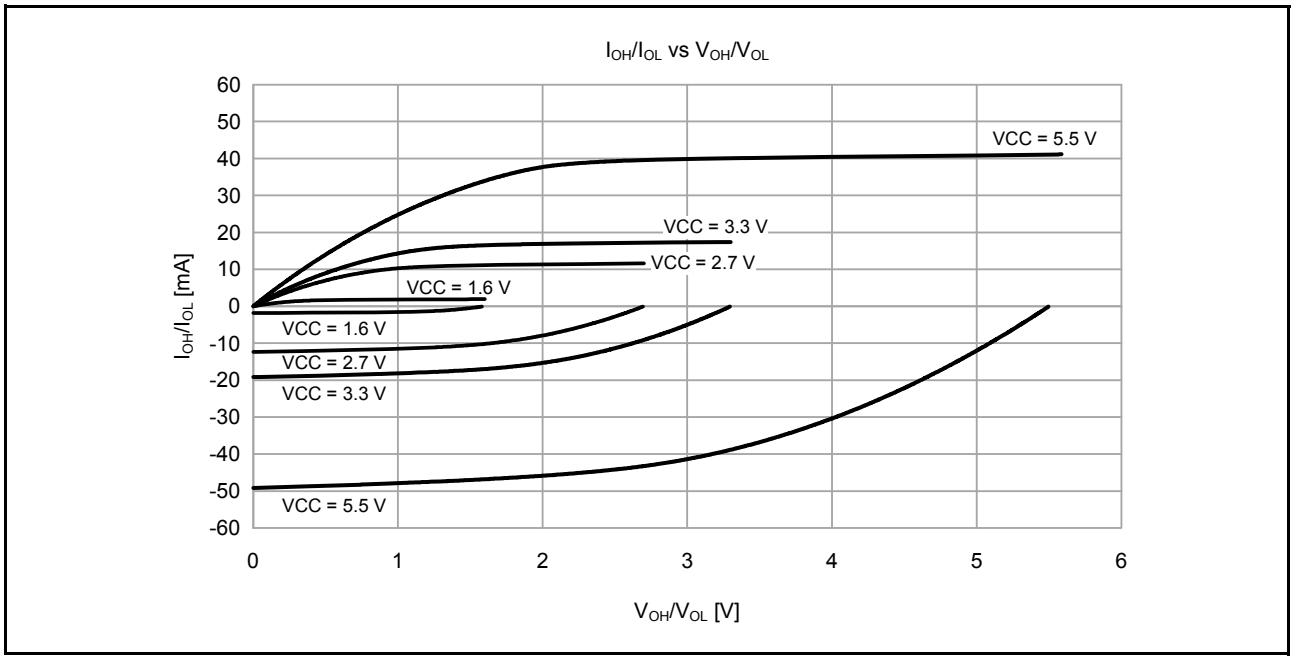

Figure 2.2 **V_{OH}/V_{OL} and I_{OH}/I_{OL} voltage characteristics at Ta = 25°C when low drive output is selected (reference data)**

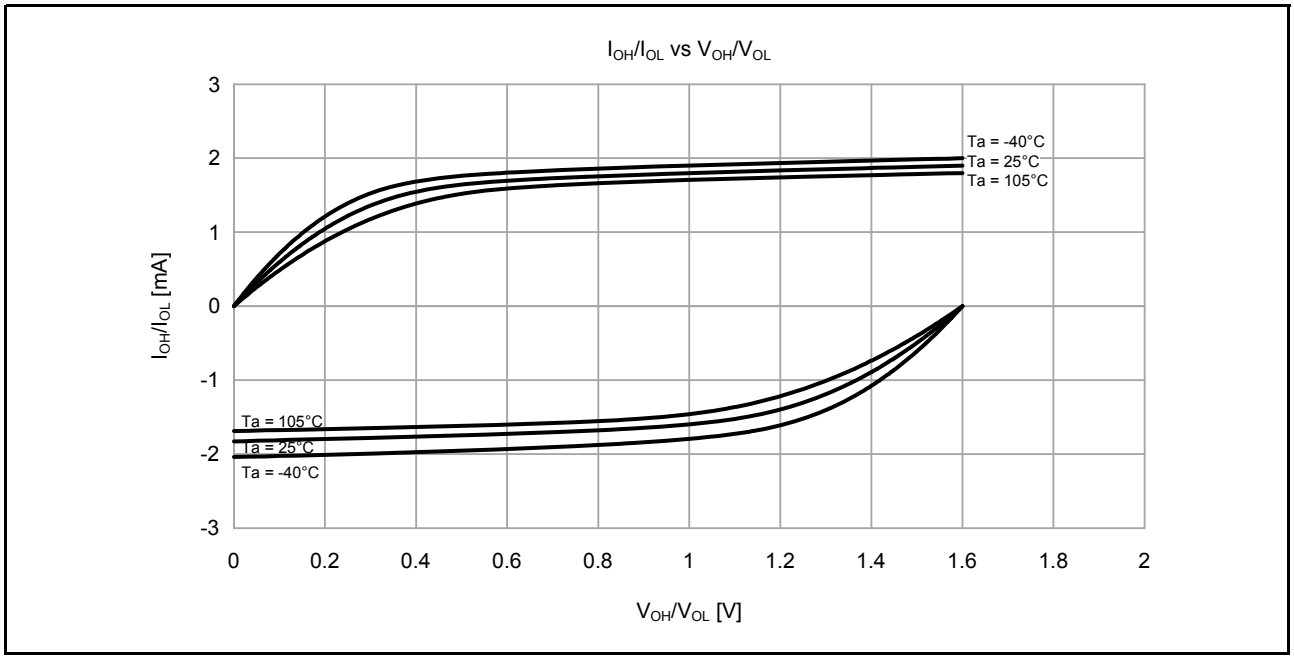

Figure 2.3 **V_{OH}/V_{OL} and I_{OH}/I_{OL} temperature characteristics at VCC = 1.6 V when low drive output is selected (reference data)**

2.2.9 Operating and Standby Current

Table 2.11 Operating and standby current (1) (1 of 2)
Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter					Symbol	Typ*9	Max	Unit	Test Conditions
Supply current*1	High-speed mode*2	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 32 MHz	I_{CC}	3.6	-	mA	*7
				ICLK = 16 MHz		2.4	-		
				ICLK = 8 MHz		1.7	-		
			All peripheral clock disabled, CoreMark code executing from flash*5	ICLK = 32 MHz		5.6	-		
				ICLK = 16 MHz		3.5	-		
				ICLK = 8 MHz		2.4	-		
			All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 32 MHz		9.5	-		*8
				ICLK = 16 MHz		5.4	-		
				ICLK = 8 MHz		3.3	-		
			All peripheral clock enabled, code executing from flash*5	ICLK = 32 MHz		-	21.0		
		Sleep mode	All peripheral clock disabled*5	ICLK = 32 MHz		1.5	-		*7
				ICLK = 16 MHz		1.1	-		
				ICLK = 8 MHz		0.9	-		
			All peripheral clock enabled*5	ICLK = 32 MHz		7.2	-		*8
				ICLK = 16 MHz		4.0	-		
				ICLK = 8 MHz		2.4	-		
		Increase during BGO operation*6				2.5	-		-
	Middle-speed mode*2	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 12 MHz	I_{CC}	1.7	-	mA	*7
				ICLK = 8 MHz		1.5	-		
			All peripheral clock disabled, CoreMark code executing from flash*5	ICLK = 12 MHz		2.7	-		
				ICLK = 8 MHz		1.9	-		
			All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 12 MHz		3.9	-		*8
				ICLK = 8 MHz		3.0	-		
			All peripheral clock enabled, code executing from flash*5	ICLK = 12 MHz		-	8.0		
		Sleep mode	All peripheral clock disabled*5	ICLK = 12 MHz		0.8	-		*7
				ICLK = 8 MHz		0.8	-		
			All peripheral clock enabled*5	ICLK = 12 MHz		2.9	-		*8
				ICLK = 8 MHz		2.2	-		
		Increase during BGO operation*6				2.5	-		-
	Low-speed mode*3	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 1 MHz	I_{CC}	0.2	-	mA	*7
			All peripheral clock disabled, CoreMark code executing from flash*5	ICLK = 1 MHz		0.3	-		
			All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 1 MHz		0.4	-		*8
			All peripheral clock enabled, code executing from flash*5	ICLK = 1 MHz		-	2.0		
		Sleep mode	All peripheral clock disabled*5	ICLK = 1 MHz		0.2	-		*7
			All peripheral clock enabled*5	ICLK = 1 MHz		0.3	-		*8

Table 2.11 Operating and standby current (1) (2 of 2)
Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter					Symbol	Typ*9	Max	Unit	Test Conditions
Supply current*1	Low-voltage mode*3	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 4 MHz	I_{CC}	1.4	-	mA	*7
			All peripheral clock disabled, CoreMark code executing from flash*5	ICLK = 4 MHz		1.4	-		
			All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 4 MHz		2.1	-		*8
			All peripheral clock enabled, code executing from flash*5	ICLK = 4 MHz		-	4.0		
		Sleep mode	All peripheral clock disabled*5	ICLK = 4 MHz		0.9	-		*7
			All peripheral clock enabled*5	ICLK = 4 MHz		1.6	-		*8
	Subosc-speed mode*4	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 32.768 kHz	I_{CC}	5.9	-	μA	*7
			All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 32.768 kHz		13.0	-		*8
			All peripheral clock enabled, code executing from flash*5	ICLK = 32.768 kHz		-	55.0		
		Sleep mode	All peripheral clock disabled*5	ICLK = 32.768 kHz		3.2	-		*7
			All peripheral clock enabled*5	ICLK = 32.768 kHz		10.0	-		*8

Note 1. Supply current values do not include output charge/discharge current from all pins. The values apply when internal pull-up MOSs are in the off state.
Note 2. The clock source is HOCO.
Note 3. The clock source is MOCO.
Note 4. The clock source is the sub-clock oscillator.
Note 5. This does not include BGO operation.
Note 6. This is the increase for programming or erasure of the flash memory for data storage during program execution.
Note 7. PCLKB and PCLKD are set to divided by 64.
Note 8. PCLKB and PCLKD are the same frequency as that of ICLK.
Note 9. VCC = 3.3 V.

2.2.10 VCC Rise and Fall Gradient and Ripple Frequency

Table 2.14 Rise and fall gradient characteristics
Conditions: VCC = AVCC0 = 0 to 5.5 V

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
Power-on VCC rising gradient	Voltage monitor 0 reset disabled at startup	SrVCC	0.02	-	2	ms/V	-
	Voltage monitor 0 reset enabled at startup*1, *2		0.02	-	-		
	SCI Boot mode*2		0.02	-	2		

Note 1. When OFS1.LVDAS = 0.
Note 2. At boot mode, the reset from voltage monitor 0 is disabled regardless of the value of OFS1.LVDAS bit.

Table 2.15 Rising and falling gradient and ripple frequency characteristics
Conditions: VCC = AVCC0 = 1.6 to 5.5 V
The ripple voltage must meet the allowable ripple frequency $f_{r(VCC)}$ within the range between the VCC upper limit (5.5 V) and lower limit (1.6 V).
When the VCC change exceeds VCC ±10%, the allowable voltage change rising and falling gradient dt/dVCC must be met.

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Allowable ripple frequency	$f_{r\ (VCC)}$	-	-	10	kHz	Figure 2.24 $V_{r\ (VCC)} \leq VCC \times 0.2$
		-	-	1	MHz	Figure 2.24 $V_{r\ (VCC)} \leq VCC \times 0.08$
		-	-	10	MHz	Figure 2.24 $V_{r\ (VCC)} \leq VCC \times 0.06$
Allowable voltage change rising and falling gradient	dt/dVCC	1.0	-	-	ms/V	When VCC change exceeds VCC ±10%

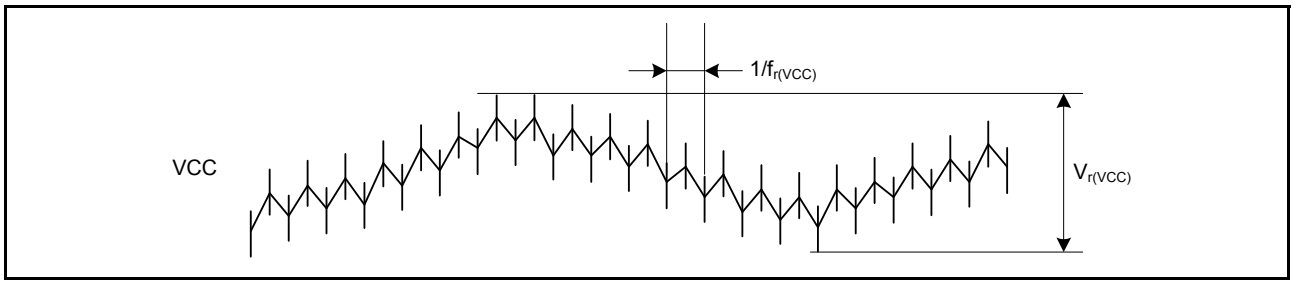

Figure 2.24 Ripple waveform

2.3 AC Characteristics

2.3.1 Frequency

Table 2.16 Operation frequency in high-speed operating mode
Conditions: VCC = AVCC0 = 2.4 to 5.5 V

Parameter			Symbol	Min	Typ	Max*5	Unit
Operation frequency	System clock (ICLK)*1, *2, *4	2.7 to 5.5 V	f	0.032768	-	32	MHz
		2.4 to 2.7 V		0.032768	-	16	
	Peripheral module clock (PCLKB)*4	2.7 to 5.5 V		-	-	32	
		2.4 to 2.7 V		-	-	16	
	Peripheral module clock (PCLKD)*3, *4	2.7 to 5.5 V		-	-	64	
		2.4 to 2.7 V		-	-	16	

Note 1. The lower-limit frequency of ICLK is 1 MHz while programming or erasing the flash memory. When using ICLK for programming or erasing the flash memory at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
Note 2. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.
Note 3. The lower-limit frequency of PCLKD is 4 MHz at 2.4 V or above and 1 MHz at below 2.4 V when the 14-bit A/D converter is in use.
Note 4. See section 8, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKB, and PCLKD.
Note 5. The maximum value of operation frequency does not include internal oscillator errors. For details on the range of guaranteed operation, see Table 2.21, Clock timing.

Table 2.17 Operation frequency in middle-speed mode
Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Parameter			Symbol	Min	Typ	Max*5	Unit
Operation frequency	System clock (ICLK)*1, *2, *4	2.7 to 5.5 V	f	0.032768	-	12	MHz
		2.4 to 2.7 V		0.032768	-	12	
		1.8 to 2.4 V		0.032768	-	8	
	Peripheral module clock (PCLKB)*4	2.7 to 5.5 V		-	-	12	
		2.4 to 2.7 V		-	-	12	
		1.8 to 2.4 V		-	-	8	
	Peripheral module clock (PCLKD)*3, *4	2.7 to 5.5 V		-	-	12	
		2.4 to 2.7 V		-	-	12	
		1.8 to 2.4 V		-	-	8	

Note 1. The lower-limit frequency of ICLK is 1 MHz while programming or erasing the flash memory. When using ICLK for programming or erasing the flash memory at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
Note 2. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.
Note 3. The lower-limit frequency of PCLKD is 4 MHz at 2.4 V or above and 1 MHz at below 2.4 V when the 14-bit A/D converter is in use.
Note 4. See section 8, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKB, and PCLKD.
Note 5. The maximum value of operation frequency does not include internal oscillator errors. For details on the range of guaranteed operation, see Table 2.21, Clock timing.

2.3.5 NMI and IRQ Noise Filter

Table 2.29 NMI and IRQ noise filter

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	
NMI pulse width	t_{NMIW}	200	-	-	ns	NMI digital filter disabled	$t_{Pcyc} \times 2 \leq 200$ ns
		$t_{Pcyc} \times 2$*1	-	-			$t_{Pcyc} \times 2 > 200$ ns
		200	-	-		NMI digital filter enabled	$t_{NMICK} \times 3 \leq 200$ ns
		$t_{NMICK} \times 3.5$*2	-	-			$t_{NMICK} \times 3 > 200$ ns
IRQ pulse width	t_{IRQW}	200	-	-	ns	IRQ digital filter disabled	$t_{Pcyc} \times 2 \leq 200$ ns
		$t_{Pcyc} \times 2$*1	-	-			$t_{Pcyc} \times 2 > 200$ ns
		200	-	-		IRQ digital filter enabled	$t_{IRQCK} \times 3 \leq 200$ ns
		$t_{IRQCK} \times 3.5$*3	-	-			$t_{IRQCK} \times 3 > 200$ ns

Note: 200 ns minimum in Software Standby mode.
Note 1. t_{Pcyc} indicates the PCLKB cycle.
Note 2. t_{NMICK} indicates the cycle of the NMI digital filter sampling clock.
Note 3. t_{IRQCK} indicates the cycle of the IRQi digital filter sampling clock (i = 0 to 7).

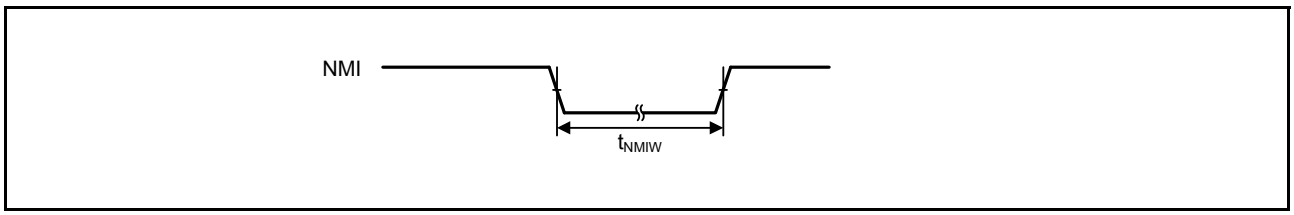

Figure 2.33 NMI interrupt input timing

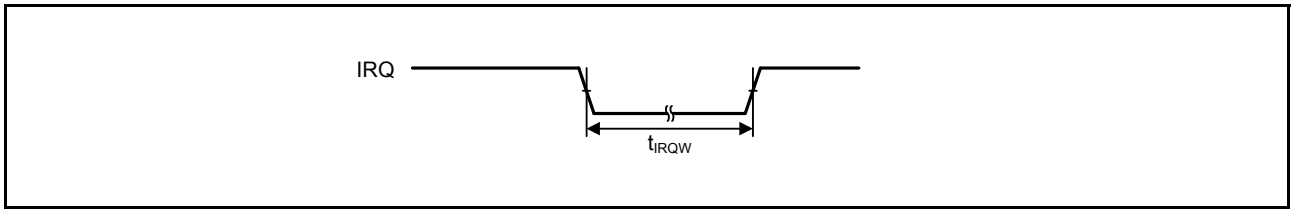

Figure 2.34 IRQ interrupt input timing

Table 2.35 SPI timing (2 of 2)

Conditions: Middle drive output is selected in the Port Drive Capability bit in the PmnPFS register.

Parameter				Symbol	Min	Max	Unit*1	Test conditions
SPI	Data output delay	Master	2.7V or above	t_{OD}	-	14	ns	Figure 2.50 to Figure 2.55 C = 30pF
			2.4V or above		-	20		
			1.8V or above		-	25		
			1.6V or above		-	30		
		Slave	2.7V or above		-	50		
			2.4V or above		-	60		
			1.8V or above		-	85		
			1.6V or above		-	110		
	Data output hold time	Master		t_{OH}	0	-	ns	
		Slave			0	-		
	Successive transmission delay	Master		t_{TD}	t_{SPcyc} + 2 × t_{Pcyc}	8 × t_{SPcyc} + 2 × t_{Pcyc}	ns	
		Slave			6 × t_{Pcyc}	-		
	MOSI and MISO rise and fall time	Output	2.7V or above	t_{Dr}, t_{Df}	-	10	ns	
			2.4V or above		-	15		
			1.8V or above		-	20		
			1.6V or above		-	30		
		Input			-	1	µs	
	SSL rise and fall time	Output	2.7V or above	t_{SSLr}, t_{SSLf}	-	10	ns	
			2.4V or above		-	15		
			1.8V or above		-	20		
			1.6V or above		-	30		
		Input			-	1	µs	
	Slave access time		2.4V or above	t_{SA}	-	2 × t_{Pcyc} +100	ns	Figure 2.54 and Figure 2.55 C = 30pF
			1.8V or above		-	2 × t_{Pcyc} +140		
			1.6V or above		-	2 × t_{Pcyc} +180		
	Slave output release time		2.4V or above	t_{REL}	-	2 × t_{Pcyc} +100	ns	
			1.8V or above		-	2 × t_{Pcyc} +140		
			1.6V or above		-	2 × t_{Pcyc} +180		

Note 1. t_{Pcyc}: PCLKB cycle.

Note 2. N is set as an integer from 1 to 8 by the SPCKD register.

Note 3. N is set as an integer from 1 to 8 by the SSLND register.

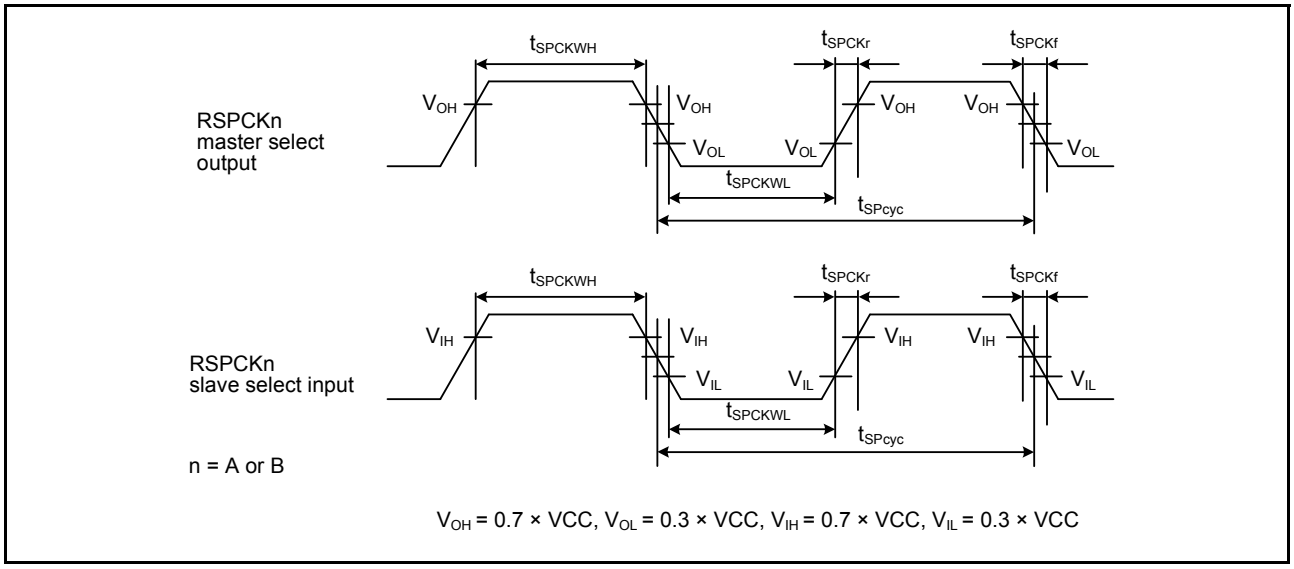

Figure 2.49 SPI clock timing

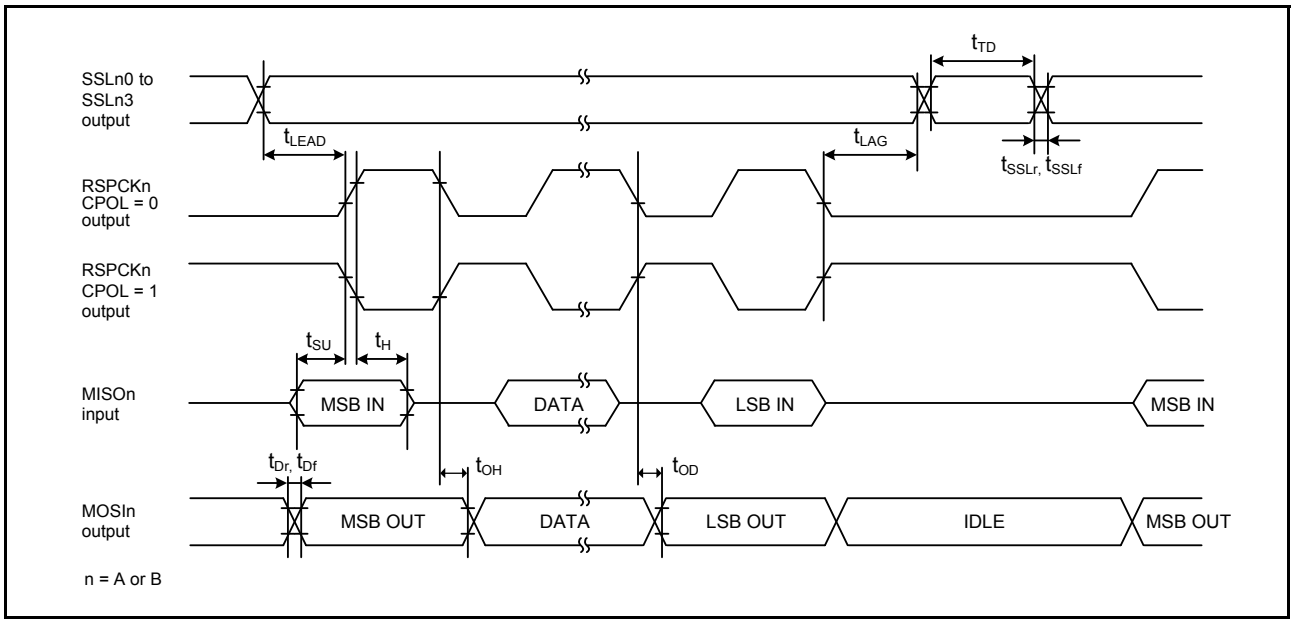

Figure 2.50 SPI timing (master, CPHA = 0) (bit rate: PCLKB division ratio is set to any value other than 1/2)

Table 2.45 A/D conversion characteristics (6) in low-power A/D conversion mode (2 of 2)
Conditions: VCC = AVCC0 = 1.8 to 5.5 V (AVCC0 = VCC when VCC < 2.0 V), VREFH0 = 1.8 to 5.5 V, VSS = AVSS0 = VREFL0 = 0 V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test Conditions
Conversion time*1 (Operation at PCLKD = 8 MHz)	Permissible signal source impedance Max. = 5 kΩ	6.75	-	-	µs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
		10.13	-	-	µs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error		-	±1.0	±7.5	LSB	High-precision channel
				±10.0	LSB	Other than above
Full-scale error		-	±1.5	±7.5	LSB	High-precision channel
				±10.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±3.0	±8.0	LSB	High-precision channel
				±12.0	LSB	Other than above
DNL differential nonlinearity error		-	±1.0	-	LSB	-
INL integral nonlinearity error		-	±1.0	±3.0	LSB	-
14-bit mode						
Resolution		-	-	14	Bit	-
Conversion time*1 (Operation at PCLKD = 8 MHz)	Permissible signal source impedance Max. = 5 kΩ	7.50	-	-	µs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
		10.88	-	-	µs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error		-	±4.0	±30.0	LSB	High-precision channel
				±40.0	LSB	Other than above
Full-scale error		-	±6.0	±30.0	LSB	High-precision channel
				±40.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±12.0	±32.0	LSB	High-precision channel
				±48.0	LSB	Other than above
DNL differential nonlinearity error		-	±4.0	-	LSB	-
INL integral nonlinearity error		-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.
Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.
Note 2. Except for I/O input capacitance (Cin), see section 2.2.4, I/O VOH, VOL, and Other Characteristics.
Note 3. Reference data.

Table 2.46 A/D conversion characteristics (7) in low-power A/D conversion mode (1 of 2)
Conditions: VCC = AVCC0 = 1.6 to 5.5 V (AVCC0 = VCC when VCC < 2.0 V), VREFH0 = 1.6 to 5.5 V, VSS = AVSS0 = VREFL0 = 0
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test Conditions
Frequency		1	-	4	MHz	-
Analog input capacitance*2	Cs	-	-	8*3	pF	High-precision channel
		-	-	9*3	pF	Normal-precision channel
Analog input resistance	Rs	-	-	13.1*3	kΩ	High-precision channel
		-	-	14.3*3	kΩ	Normal-precision channel

Table 2.46 A/D conversion characteristics (7) in low-power A/D conversion mode (2 of 2)
Conditions: VCC = AVCC0 = 1.6 to 5.5 V (AVCC0 = VCC when VCC < 2.0 V), VREFH0 = 1.6 to 5.5 V, VSS = AVSS0 = VREFL0 = 0
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter			Min	Typ	Max	Unit	Test Conditions
Analog input voltage range		Ain	0	-	VREFH0	V	-
12-bit mode							
Resolution			-	-	12	Bit	-
Conversion time*1 (Operation at PCLKD = 4 MHz)	Permissible signal source impedance Max. = 9.9 kΩ		13.5	-	-	μs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
			20.25	-	-	μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error			-	±1.0	±7.5	LSB	High-precision channel
					±10.0	LSB	Other than above
Full-scale error			-	±1.5	±7.5	LSB	High-precision channel
					±10.0	LSB	Other than above
Quantization error			-	±0.5	-	LSB	-
Absolute accuracy			-	±3.0	±8.0	LSB	High-precision channel
					±12.0	LSB	Other than above
DNL differential nonlinearity error			-	±1.0	-	LSB	-
INL integral nonlinearity error			-	±1.0	±3.0	LSB	-
14-bit mode							
Resolution			-	-	14	Bit	-
Conversion time*1 (Operation at PCLKD = 4 MHz)	Permissible signal source impedance Max. = 9.9 kΩ		15.0	-	-	μs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
			21.75	-	-	μs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error			-	±4.0	±30.0	LSB	High-precision channel
					±40.0	LSB	Other than above
Full-scale error			-	±6.0	±30.0	LSB	High-precision channel
					±40.0	LSB	Other than above
Quantization error			-	±0.5	-	LSB	-
Absolute accuracy			-	±12.0	±32.0	LSB	High-precision channel
					±48.0	LSB	Other than above
DNL differential nonlinearity error			-	±4.0	-	LSB	-
INL integral nonlinearity error			-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.
Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.
Note 2. Except for I/O input capacitance (Cin), see section 2.2.4, I/O VOH, VOL, and Other Characteristics.
Note 3. Reference data.

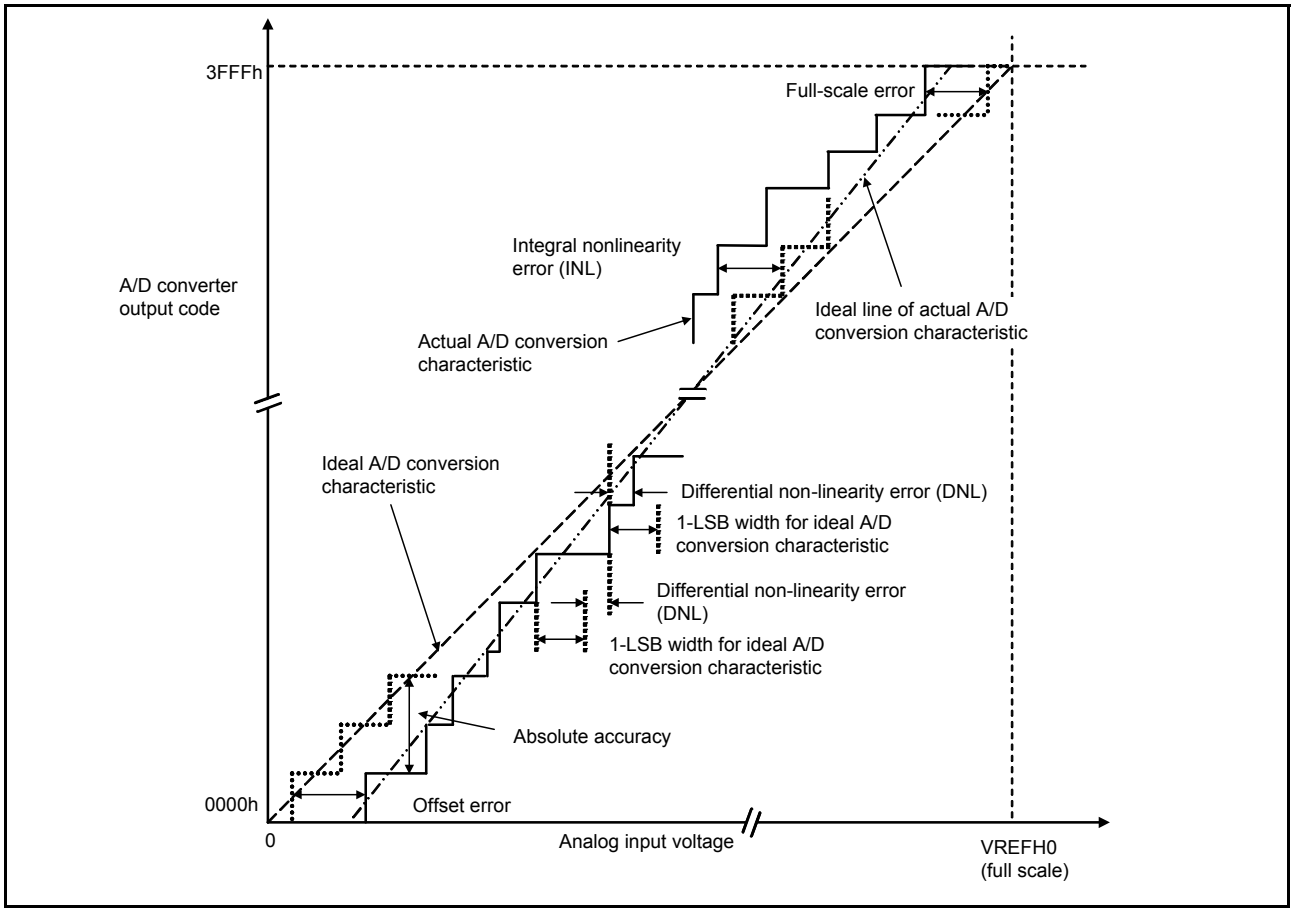

Figure 2.63 Illustration of 14-bit A/D converter characteristic terms

Absolute accuracy

Absolute accuracy is the difference between output code based on the theoretical A/D conversion characteristics, and the actual A/D conversion result. When measuring absolute accuracy, the voltage at the midpoint of the width of the analog input voltage (1-LSB width), which can meet the expectation of outputting an equal code based on the theoretical A/D conversion characteristics, is used as the analog input voltage. For example, if 12-bit resolution is used and the reference voltage VREFH0 = 3.072 V, then 1-LSB width becomes 0.75 mV, and 0 mV, 0.75 mV, and 1.5 mV are used as the analog input voltages. If analog input voltage is 6 mV, an absolute accuracy of ±5 LSB means that the actual A/D conversion result is in the range of 003h to 00Dh, though an output code of 008h can be expected from the theoretical A/D conversion characteristics.

Integral nonlinearity error (INL)

Integral nonlinearity error is the maximum deviation between the ideal line when the measured offset and full-scale errors are zeroed, and the actual output code.

Differential nonlinearity error (DNL)

Differential nonlinearity error is the difference between 1-LSB width based on the ideal A/D conversion characteristics and the width of the actual output code.

Offset error

Offset error is the difference between the transition point of the ideal first output code and the actual first output code.

Full-scale error

Full-scale error is the difference between the transition point of the ideal last output code and the actual last output code.

Table 2.58 Code flash characteristics (3)

Middle-speed operating mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V, Ta = -40 to +85°C

Parameter		Symbol	ICLK = 1 MHz			ICLK = 8 MHz			Unit
			Min	Typ	Max	Min	Typ	Max	
Programming time	4-byte	t_{P4}	-	157	1411	-	101	966	µs
Erasure time	1-KB	t_{E1K}	-	9.10	289	-	6.10	228	ms
Blank check time	2-byte	t_{BC4}	-	-	87.7	-	-	52.5	µs
	1-KB	t_{BC1K}	-	-	1930	-	-	414	µs
Erase suspended time		t_{SED}	-	-	32.7	-	-	21.6	µs
Startup area switching setting time		t_{SAS}	-	22.8	592	-	14.2	465	ms
Access window time		t_{AWS}	-	22.8	592	-	14.2	465	ms
OCD/serial programmer ID setting time		t_{OSIS}	-	22.8	592	-	14.2	465	ms
Flash memory mode transition wait time 1		t_{DIS}	2	-	-	2	-	-	µs
Flash memory mode transition wait time 2		t_{MS}	720	-	-	720	-	-	ns

Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.

Note 2. The lower-limit frequency of ICLK is 1 MHz during programming or erasing the flash memory. When using ICLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note 3. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.

2.12.2 Data Flash Memory Characteristics

Table 2.59 Data flash characteristics (1)

Parameter		Symbol	Min	Typ	Max	Unit	Conditions
Reprogramming/erasure cycle*1		N_{DPEC}	100000	1000000	-	Times	-
Data hold time	After 10000 times of N_{DPEC}	t_{DDRP}	20*2, *3	-	-	Year	Ta = +85°C
	After 100000 times of N_{DPEC}		5*2, *3	-	-	Year	
	After 1000000 times of N_{DPEC}		-	1*2, *3	-	Year	Ta = +25°C

Note 1. The reprogram/erase cycle is the number of erasure for each block. When the reprogram/erase cycle is n times (n = 100,000), erasing can be performed n times for each block. For instance, when 1-byte programming is performed 1,000 times for different addresses in 1-byte blocks, and then the entire block is erased, the reprogram/erase cycle is counted as 1. However, programming the same address for several times as one erasure is not enabled. (overwriting is prohibited.)

Note 2. Characteristics when using the flash memory programmer and the self-programming library provided by Renesas Electronics.

Note 3. These results are obtained from reliability testing.

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S124 Microcontroller Group

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R01DS0264EU0130